**Product data sheet** 

# 1. General description

WeEn's 5th Generation Hyper Fast diode with softer recovery in a 2-lead IITO220 plastic package.

### 2. Features and benefits

- Isolated mounting base with 2500 V (RMS) isolation
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- · Soft reverse recovery with low recovery current
- · Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit	
Absolute	maximum rating							
$V_{RRM}$	repetitive peak reverse voltage				600		V	
$I_{F(AV)}$	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		30			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 $\mu$ s; square-wave pulse		60			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270		А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			300		А	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static ch	aracteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.00	2.75	V	
Dynamic	Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/µs}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	18	22	ns	

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode		K — A
mb	n.c.	mounting base; isolated	ITO220-2L	001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number		Small packing quantity	Package version	Package issue date
BYC30MY-600PS	IITO220-2L	BYC30MY-600PSQ	Tube	50	IITO220E-2L	03-Mar-2020

## 7. Marking

#### Table 4. Marking codes

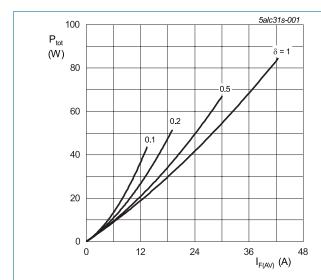
Type number	Marking codes
BYC30MY-600PS	BYC30MY 600PS

# 8. Limiting values

### **Table 5. Limiting values**

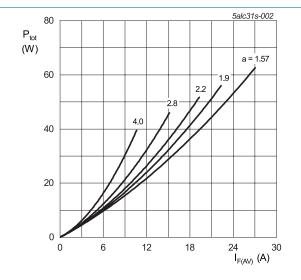
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			600	V
$V_{RWM}$	crest working reverse voltage			600	V
$V_R$	reverse voltage	DC		600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		30	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 µs; square-wave pulse		60	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		300	Α
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



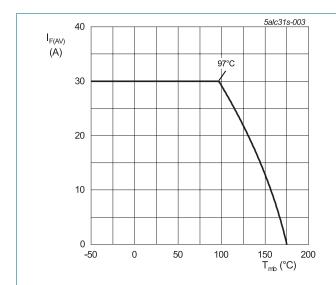
 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V<sub>o</sub> = 1.410 V; R<sub>s</sub> = 0.0136 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.410 V;  $R_s$  = 0.0136  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





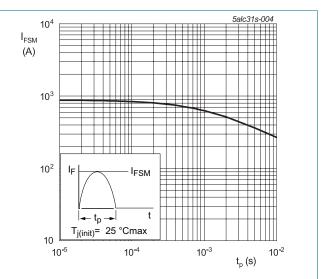
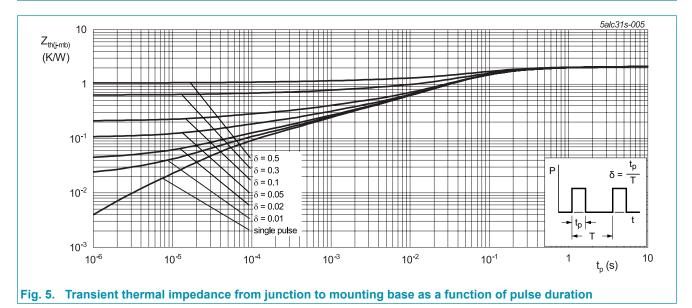


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5		-	-	2.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W



## 10. Isolation characteristics

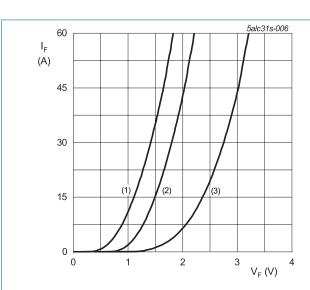
#### **Table 7. Isolation characteristics**

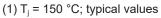
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

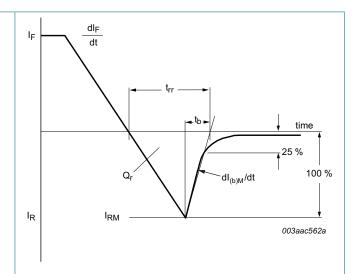
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.00	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.40	1.80	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C		-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C		-	-	1	mA
Dynamic	characteristics				•		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	18	22	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	70	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.5	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	7.6	-	А
Q <sub>r</sub>	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 \text{ °C}; Fig. 7$		-	50	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_J = 125 ^{\circ}\text{C}; Fig. 7$		-	280	-	nC
S <sub>factor</sub>	softness factor	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$		-	0.26	-	





<sup>(2)</sup> T<sub>i</sub> = 150 °C; maximum values

Fig. 6. Forward current as a function of forward voltage



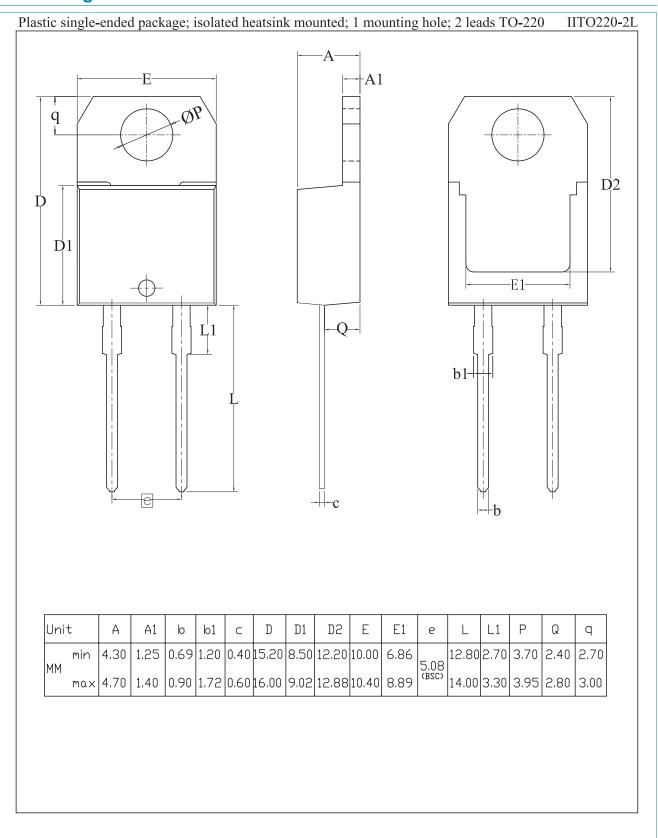
$$\begin{split} S_{\text{factor}} &= \left[ \text{dI}_{\text{F}} / \text{dt} \right] / \left[ \text{dI}_{\text{(b)M}} / \text{dt} \right] \\ \text{dI}_{\text{(b)M}} / \text{dt} &= \text{peak rate of change of current during } t_{\text{b}} \\ \text{portion of } t_{\text{rr}} \end{split}$$

Fig. 7. Reverse recovery definitions; ramp recovery

<sup>(3)</sup>  $T_j = 25$  °C; maximum values

 $V_0 = 1.410 \text{ V}; R_s = 0.0136 \Omega$ 

# 12. Package outline



## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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